

# C106 Series

## Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

Glassivated PNP devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

### Features

- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
- These are Pb-Free Devices

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Max	Unit
Peak Repetitive Off-State Voltage (Note 1) (Sine Wave, 50–60 Hz, $R_{GK} = 1\text{ k}\Omega$ , $T_C = -40^\circ$ to $110^\circ\text{C}$ )	$V_{DRM}$ , $V_{RRM}$		V
	C106B	200	
	C106D, C106D1*	400	
	C106M, C106M1*	600	
On-State RMS Current ( $180^\circ$ Conduction Angles, $T_C = 80^\circ\text{C}$ )	$I_{T(RMS)}$	4.0	A
Average On-State Current ( $180^\circ$ Conduction Angles, $T_C = 80^\circ\text{C}$ )	$I_{T(AV)}$	2.55	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = +25^\circ\text{C}$ )	$I_{TSM}$	20	A
Circuit Fusing Considerations ( $t = 8.3\text{ ms}$ )	$I^2t$	1.65	$\text{A}^2\text{s}$
Forward Peak Gate Power (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$ , $T_C = 80^\circ\text{C}$ )	$P_{GM}$	0.5	W
Forward Average Gate Power (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$ , $T_C = 80^\circ\text{C}$ )	$P_{G(AV)}$	0.1	W
Forward Peak Gate Current (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$ , $T_C = 80^\circ\text{C}$ )	$I_{GM}$	0.2	A
Operating Junction Temperature Range	$T_J$	-40 to +110	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Mounting Torque (Note 2)	-	6.0	in. lb.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

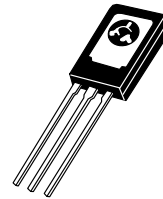
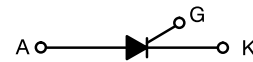
1.  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.



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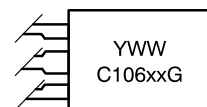
SCRs  
4 A RMS, 200 – 600 Volts



TO-225AA  
CASE 077  
STYLE 2

### MARKING DIAGRAM & PIN ASSIGNMENT

1. Cathode
2. Anode
3. Gate



Y = Year  
WW = Work Week  
C106xx = Device Code  
xx = B, D, D1, M, M1  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## C106 Series

### Thermal Characteristics (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3.0	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8 in. from Case for 10 Seconds	T <sub>L</sub>	260	°C

### Electrical Characteristics (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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#### OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (V <sub>AK</sub> = Rated V <sub>DRM</sub> or V <sub>RRM</sub> , R <sub>GK</sub> = 1 kΩ)	I <sub>DRM</sub> , I <sub>RRM</sub>	T <sub>J</sub> = 25°C	-	-	10	μA
		T <sub>J</sub> = 110°C	-	-	100	μA

#### ON CHARACTERISTICS

Peak Forward On-State Voltage (Note 3) (I <sub>TM</sub> = 4 A)	V <sub>TM</sub>	-	-	2.2	V	
Gate Trigger Current (Continuous dc) (Note 4) (V <sub>AK</sub> = 6 Vdc, R <sub>L</sub> = 100 Ω)	I <sub>GT</sub>	T <sub>J</sub> = 25°C	-	15	200	μA
		T <sub>J</sub> = -40°C	-	35	500	
Peak Reverse Gate Voltage (I <sub>GR</sub> = 10 μA)	V <sub>GRM</sub>	-	-	6.0	V	
Gate Trigger Voltage (Continuous dc) (Note 4) (V <sub>AK</sub> = 6 Vdc, R <sub>L</sub> = 100 Ω)	V <sub>GT</sub>	T <sub>J</sub> = 25°C	0.4	0.60	0.8	V
		T <sub>J</sub> = -40°C	0.5	0.75	1.0	
Gate Non-Trigger Voltage (Continuous dc) (Note 4) (V <sub>AK</sub> = 12 V, R <sub>L</sub> = 100 Ω, T <sub>J</sub> = 110°C)	V <sub>GD</sub>	0.2	-	-	V	
Latching Current (V <sub>AK</sub> = 12 V, I <sub>G</sub> = 20 mA, R <sub>GK</sub> = 1 kΩ)	I <sub>L</sub>	T <sub>J</sub> = 25°C	-	0.20	5.0	mA
		T <sub>J</sub> = -40°C	-	0.35	7.0	
Holding Current (V <sub>D</sub> = 12 Vdc) (Initiating Current = 20 mA, R <sub>GK</sub> = 1 kΩ)	I <sub>H</sub>	T <sub>J</sub> = 25°C	-	0.19	3.0	mA
		T <sub>J</sub> = -40°C	-	0.33	6.0	
		T <sub>J</sub> = +110°C	-	0.07	2.0	

#### DYNAMIC CHARACTERISTICS

Critical Rate-of-Rise of Off-State Voltage (V <sub>AK</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, R <sub>GK</sub> = 1 kΩ, T <sub>J</sub> = 110°C)	dv/dt	-	8.0	-	V/μs
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3. Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.
4. R<sub>GK</sub> is not included in measurement.

# C106 Series

## Voltage Current Characteristic of SCR

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Peak On State Voltage
$I_H$	Holding Current

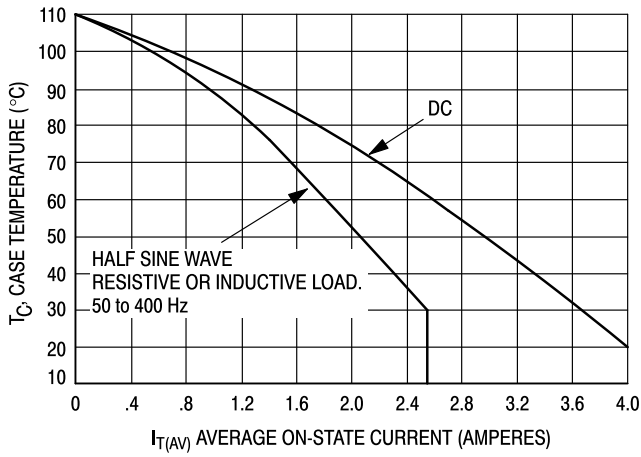
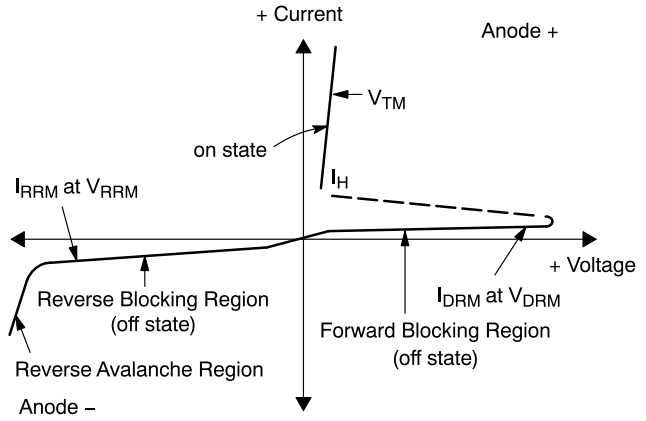


Figure 1. Average Current Derating

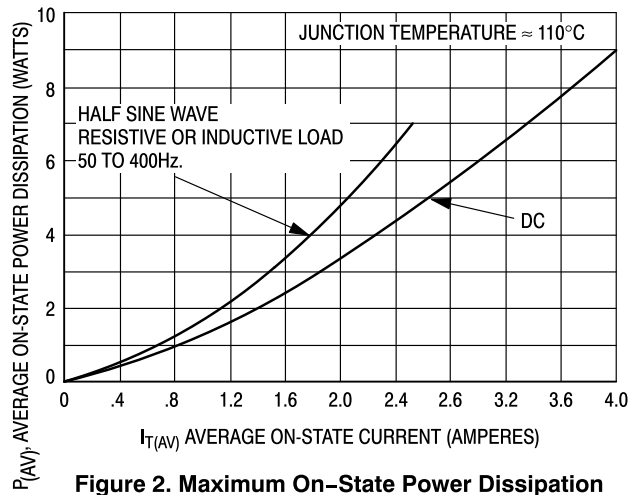
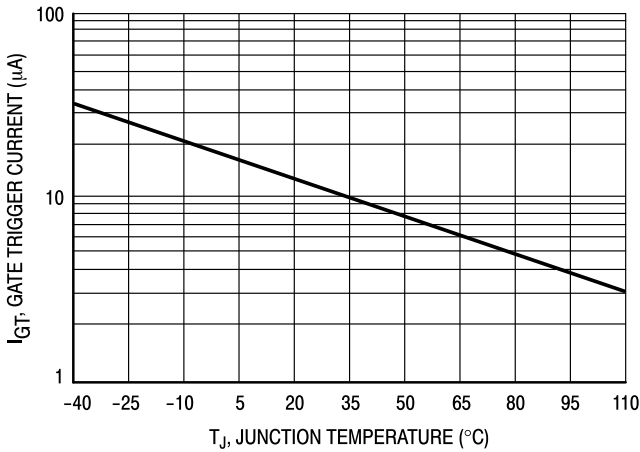
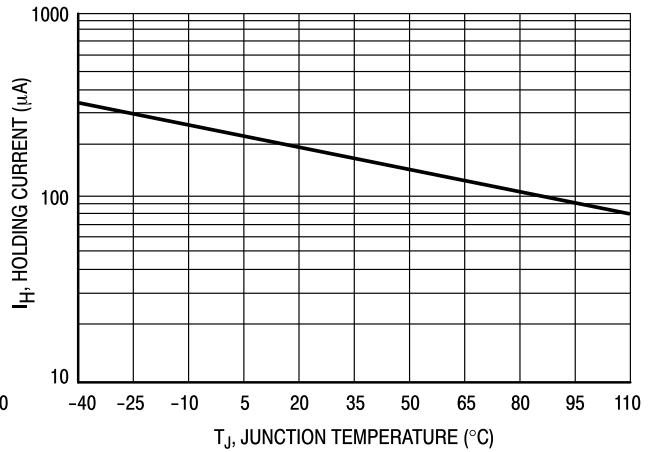


Figure 2. Maximum On-State Power Dissipation

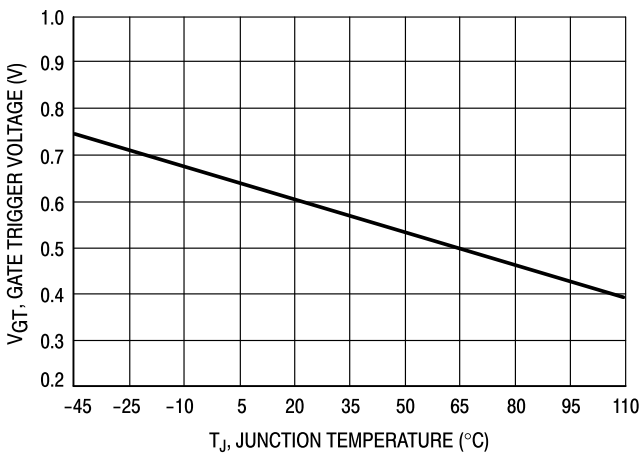
## C106 Series



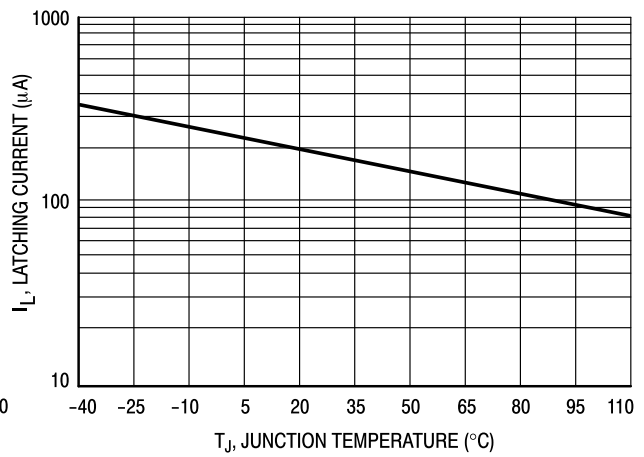
**Figure 3. Typical Gate Trigger Current versus Junction Temperature**



**Figure 4. Typical Holding Current versus Junction Temperature**



**Figure 5. Typical Gate Trigger Voltage versus Junction Temperature**



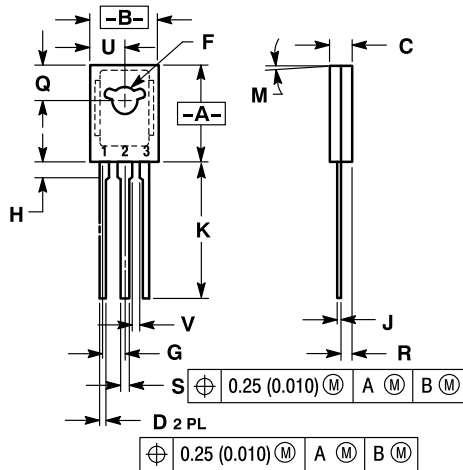
**Figure 6. Typical Latching Current versus Junction Temperature**



# C106 Series

## PACKAGE DIMENSIONS

TO-225  
CASE 77-09  
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 2:

- PIN 1. CATHODE
- ANODE
- GATE

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